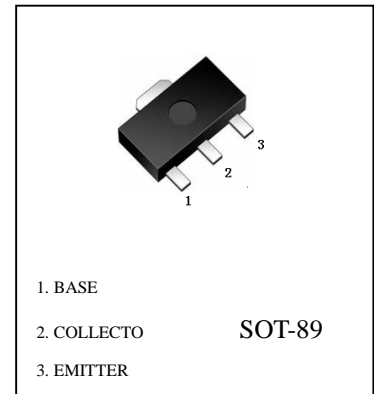


FEATURES

- Epitaxial planar die construction.
- Complementary NPN type available PXT2222A.
- Ideal for medium power amplification and switching.

PXT2907A(PNP)

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-600	mA
Collector Power Dissipation	P_C	500	mW
Storage Temperature	T_{stg}	-55-150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=-10\mu A$ $I_E=0$	-60		V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=-10mA$ $I_B=0$	-60		V
Emitter-base breakdown voltage	V_{EBO}	$I_E=-10\mu A$ $I_C=0$	-5		μV
Collector cut-off current	I_{CBO}	$V_{CB}=-50V$ $I_E=0$		-10	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V$ $I_C=0$		-50	nA
DC current gain	h_{FE}	$V_{CE}=-1V$ $I_C=-100mA$ $V_{CE}=-1V$ $I_C=-1mA$ $V_{CE}=-1V$ $I_C=-10mA$ $V_{CE}=-2V$ $I_C=-150mA$ $V_{CE}=-10V$ $I_C=-500mA$	75 100 100 100 50	- -300 -	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-150mA$ $I_B=-15mA$ $I_C=-500mA$ $I_B=-50mA$		-0.4 -1.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-150mA$ $I_B=-15mA$ $I_C=-500mA$ $I_B=-50mA$		-1.3 -2.6	V
Transition frequency	f_T	$V_{CE}=-10V$	200		MHz
Output Capacitance	C_{obo}	$V_{CB}=-10V$ $f=1.0MHz$ $I_E=0$	-	8.0	pF
Input Capacitance	C_{ibo}	$V_{EB}=-10V$ $f=1.0MHz$ $I_C=0$	-	30	pF
Delay time	t_d	$V_{CE}=-30V$, $I_C=-150mA$, $I_{B1}=-15mA$		10	ns
Rise time	t_r			40	ns
Storage time	t_s	$V_{CE}=-6V$, $I_C=-150mA$ $I_{B1}=-I_{B2}=-15mA$		80	ns
Fall time	t_f			30	ns

PXT2907A Typical Characteristics

